

PATENT ASSIGNMENT

Electronic Version v1.1
Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	RELEASE BY SECURED PARTY
CONVEYING PARTY DATA	
Name	Execution Date
BLUECREST VENTURE FINANCE MASTER FUND LIMITED	07/18/2011
RECEIVING PARTY DATA	
Name:	SEMISOUTH LABORATORIES, INC.
Street Address:	ONE RESEARCH BLVD., SUITE 201B
City:	STARKVILLE
State/Country:	MISSISSIPPI
Postal Code:	39759
PROPERTY NUMBERS Total: 29	
Property Type	Number
Patent Number:	6693308
Patent Number:	6815304
Patent Number:	7119380
Patent Number:	7202528
Patent Number:	7556994
Patent Number:	7242040
Patent Number:	7470967
Patent Number:	7510921
Patent Number:	7294860
Patent Number:	7416929
Patent Number:	7314799
Patent Number:	7274083
Patent Number:	7560325
Patent Number:	7602228
Application Number:	11198298

501605107

PATENT
REEL: 026645 FRAME: 0351

CH \$1160.00 6693308

Application Number:	12117121
Application Number:	12055725
Application Number:	12146580
Application Number:	12437173
Application Number:	11764593
Application Number:	11764606
Application Number:	11822568
Application Number:	11836994
Application Number:	11934805
Application Number:	11935442
Application Number:	12613065
Application Number:	61177014
Application Number:	61218758
Application Number:	61218751

CORRESPONDENCE DATA

Fax Number: (949)567-6710

Correspondence will be sent via US Mail when the fax attempt is unsuccessful.

Phone: (415)773-4292

Email: ipprosecution@orrick.com

Correspondent Name: Chelseaa Bush

Address Line 1: 4 PARK PLAZA, SUITE 1600

Address Line 2: ORRICK, HERRINGTON & SUTCLIFFE LLP

Address Line 4: Irvine, CALIFORNIA 92614-2558

ATTORNEY DOCKET NUMBER:	18664-1
-------------------------	---------

NAME OF SUBMITTER:	Chelseaa Bush
--------------------	---------------

Total Attachments: 4

source=Pat#page1.tif

source=Pat#page2.tif

source=Pat#page3.tif

source=Pat#page4.tif

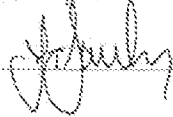
RELEASE OF SECURITY INTEREST

PATENTS

BlueCrest Venture Finance Master Fund Limited, a Cayman Islands limited company, as assignee of Ritchie Capital Finance, LLC ("Lender"), for good and valuable consideration, hereby releases and discharges its security interest in the patents, more particularly described on Schedule A annexed hereto and made a part hereof, and the goodwill associated therewith (the "Security Interest"). The Security Interest was granted to Lender by SemiSouth Laboratories, Inc., a Mississippi corporation ("Grantor"). The Security Interest is dated November 30, 2009, and was recorded December 22, 2009 at Reel 023691, Frame 0114 in the U.S. Patent and Trademark Office. The debt secured thereby has been paid and satisfied in full.

IN WITNESS WHEREOF, Lender has duly executed this Release of Security Interest as of July 18, 2011.

BlueCrest Venture Finance Master Fund Limited,
acting by its duly appointed agent, BlueCrest
Capital Management Guernsey LP (acting through
its Geneva branch) acting by its general partner
BlueCrest Capital Management Guernsey Limited

By: 
Name:
Title:

Jeremy Sambrook
Director

SCHEDULE A TO RELEASE OF SECURITY INTEREST

PATENTS AND PATENT APPLICATIONS

Title	Jurisdiction	Application No.	Filing Date	Patent No.	Issue date
Power SiC Devices Having Raised Guard Rings	US	10/079,892	02/22/2002	6,693,308	02/17/2004
SiC Bipolar Junction Transistor with Overgrown Base Region	US	10/079,893	02/22/2002	6,815,304	11/09/2004
Lateral Trench Field-Effect Transistors in Wide Band-Gap Semiconductor Materials, Methods of Making, and Integrated Circuits Incorporating the Transistors	US	10/999,954	12/01/2004	7,119,380	10/10/2006
Normally-off Integrated JFET Power Switches in WBG Semiconductors and Methods of Making	US	11/040,222	12/01/2004	7,302,528	04/10/2007
Normally-off Integrated JFET Power Switches in WBG Semiconductors and Methods of Making	US	11/783,224	04/06/2007	7,556,994	07/07/2009
Lateral Trench Field-Effect Transistors in Wide Band-Gap Semiconductor Materials, Methods of Making, and Integrated Circuits Incorporating the Transistors	US	11/505,813	08/18/2006	7,242,040	07/10/2007
Self-Aligned Silicon Carbide Semiconductor Devices and Methods of Making The Same	US	11/076,857	03/11/2005	7,470,967	12/30/2008
Self-Aligned Silicon Carbide Semiconductor Devices and Methods of Making The Same	US	11/699,509	01/30/2007	7,510,921	03/31/2009
Monolithic Vertical Junction Field Effect Transistor and Schottky Barrier Diode Fabricated from SiC and Method for Fabricating Same	US	11/176,625	07/08/2005	7,294,860	11/13/2007
Monolithic Vertical Junction Field Effect Transistor and Schottky Barrier Diode Fabricated from SiC and Method for Fabricating Same	US	11/808,701	06/12/2007	7,416,929	08/26/2008
Self-Aligned Trench Field Effect Transistors with Regrown Gates and BJTs with Regrown Base Contact Regions and Methods of Making	US	11/293,261	12/05/2005	7,314,799	01/01/2008
Semiconductor Device with Surge Current Protection and Method of Making the Same	US	11/415,279	05/02/2006	7,274,083	09/25/2007
Method of Making Lateral Junction Field Effect Transistors Using Selective Epitaxial Growth	US	12/102,382	04/14/2008	7,560,325	07/14/2009

Title	Jurisdiction	Application No.	Filing Date	Patent No.	Issue date
Half-Bridge Circuits Employing Normally On Switches and Methods of Preventing Unintended Current Flow Therein	US	11/802,388	05/21/2007	7,602,228	10/13/2009
Vertical-Channel Junction Field-Effect Transistors Having Buried Gates And Methods Of Making	US	11/198,298	08/03/2005	Pending App.	Pending App.
Semiconductor Devices with Non-Punch-Through Semiconductor Channels Having Enhanced Conduction and Methods of Making	US	12/117,121	03/08/2008	Pending App.	Pending App.
Epitaxial Growth on Low Degree Off-Axis SiC Substrates and Semiconductor Devices Made Thereby	US	12/055,725	03/26/2008	Pending App.	Pending App.
Junction Barrier Schottky Rectifiers Having Epitaxially Grown P+-N Junctions and Methods of Making	US	12/146,580	06/26/2008	Pending App.	Pending App.
High Temperature Gate Drivers for Wide Bandgap Semiconductor Power JFETS & Integrated Circuits Including the Same	US	12/437,173	05/07/2009	Pending App.	Pending App.
Silicon Carbide and Related Wide-Bandgap Transistors on Semi-Insulating Epitaxy	US	11/764,593	06/18/2007	Pending App.	Pending App.
Optically Controlled Silicon Carbide and Related Wide-Bandgap Transistors and Thyristors	US	11/764,606	06/18/2007	Pending App.	Pending App.
Normally-Off Integrated JFET Power Switches In Wide Bandgap Semiconductors And Methods Of Making	US	11/822,568	07/06/2007	Pending App.	Pending App.
Vertical Junction Field Effect Transistor with Mesa Termination and Method of Making The Same	US	11/836,994	08/10/2007	Pending App.	Pending App.
Self-Aligned Trench Field Effect Transistors With Regrown Gates And Bipolar Junction Transistors With Regrown Base Contact Regions And Methods Of Making	US	11/934,805	11/05/2007	Pending App.	Pending App.
Vertical-Channel Junction Field-Effect Transistors Having Buried Gates And Methods Of Making	US	11/935,442	11/06/2007	Pending App.	Pending App.
VJFET Having Sloped Sidewalls & Methods of Making	US	12/613,063	11/03/2009	Pending	Pending
N-Channel JFET Based Gate Driver for Enhancement-Mode & Depletion-Mode Wide Bandgap Semiconductor JFETS	US	61/177,014	05/21/2009	Pending	Pending
VJFET & Diodes Having Graded Doped Regions & Methods of Making	US	61/218,758	06/19/2009	Pending	Pending

Title	Jurisdiction	Application No.	Filing Date	Patent No.	Issue date
Methods of Making JFET & Bipolar Junction Transistors Without Ion Implantation & Devices Made Therewith	US	61/218,751	06/19/2009	Pending	Pending